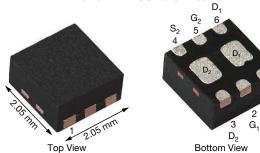


Vishay Siliconix

Dual P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A)	Q _g (TYP.)						
-20	0.054 at $V_{GS} = -4.5 \text{ V}$	-4.5 ^a							
	0.070 at V _{GS} = -2.5 V	-4.5 ^a	9.5 nC						
	0.104 at V _{GS} = -1.8 V	-4.5 ^a	9.5110						
	0.165 at $V_{GS} = -1.5 \text{ V}$	-1.5							

PowerPAK® SC-70-6L Dual



Marking Code: DP **Ordering Information:**

SiA923AEDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

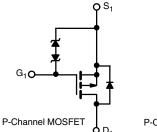
- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2500 V
- 100 % R_q Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

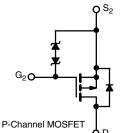


HALOGEN FREE

APPLICATIONS

- Charger Switches and Load Switches for Portable Devices
- DC/DC Converters





ABSOLUTE MAXIMUM RATINGS	$(1_A = 25 ^{\circ}\text{C}, \text{ unless})$	otherwise noted	d)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V _{GS}	± 8	V	
	T _C = 25 °C		-4.5 ^a		
Continuous Drain Comment (T. 150 °C)	T _C = 70 °C		-4.5 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	-4.5 a,b,c		
	T _A = 70 °C		-4.5 a,b,c	Α	
Pulsed Drain Current (t = 100 μs)		I _{DM}	-15		
Continuous Source-Drain Diode Current	T _C = 25 °C		-4.5 ^a		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	-1.6 ^{b,c}		
	T _C = 25 °C		7.8		
Maximum Dayyar Dissination	T _C = 70 °C		5	w	
Maximum Power Dissipation	T _A = 25 °C	P _D	1.9 b,c	VV	
	T _A = 70 °C		1.2 b,c		
Operating Junction and Storage Temperature R	Range	T _J , T _{stg}	-55 to 150	°C	
Soldering Recommendations (Peak Temperatur	re) d,e		260		

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum Junction-to-Ambient b,f	t ≤ 5 s	R _{thJA}	52	65	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	12.5	16	C/VV				

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 110 °C/W.



Vishay Siliconix

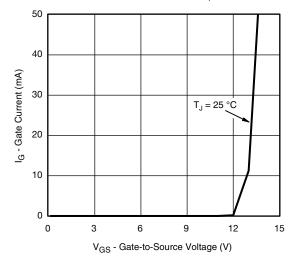
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20	_	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$		-	-15	-	mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μA	-	2.5	-	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-	-0.9	V
	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$	± 0.3	± 3		
Gate-Source Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$	_	± 3	± 30	
		V _{DS} = -20 V, V _{GS} = 0 V	-	-	-1	- μA -
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V, T _J = 55 °C	-	-	-10	
On-State Drain Current a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-15		-	Α
	(* /	V _{GS} = -4.5 V, I _D = -3.8 A	-	0.044	0.054	Ω
		$V_{GS} = -2.5 \text{ V}, I_D = -3.3 \text{ A}$	-	0.057	0.070	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -1.8 V, I _D = -1 A	-	0.075	0.104	
		V _{GS} = -1.5 V, I _D = -0.5 A	-	0.097	0.165	
Forward Transconductance a	9 _{fs}	$V_{DS} = -10 \text{ V}, I_D = -3.8 \text{ A}$	-	11	-	S
Dynamic ^b				•	l	
Input Capacitance	C _{iss}		-	770	-	
Output Capacitance	C _{oss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	-	90	-	pF
Reverse Transfer Capacitance	C _{rss}		-	81	-	
Tabal Oaks Observe	Q_g	V _{DS} = -10 V, V _{GS} = -8 V, I _D = -4.9 A	-	16.3	25	nC
Total Gate Charge			-	9.5	14.5	
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.9 \text{ A}$	-	1.4	-	
Gate-Drain Charge	Q_{gd}		-	2.3	-	
Gate Resistance	R_g	f = 1 MHz	1	5.1	10	Ω
Turn-On Delay Time	t _{d(on)}		-	15	25	
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_1 = 2.6 \Omega$	-	16	25	ns
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.9 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	30	45	
Fall Time	t _f		-	10	15	
Turn-On Delay Time	t _{d(on)}		-	7	15	
Rise Time	t _r	$V_{DD} = -10 \text{ V}, R_1 = 2.6 \Omega$	-	12	20	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -3.9 \text{ A}, V_{GEN} = -8 \text{ V}, R_g = 1 \Omega$	-	26	40	
Fall Time	t _f		-	10	15	
Drain-Source Body Diode Characterist	ics			•		
Continuous Source-Drain Diode Current	Is	T _C = 25 °C	-	-	-4.5	A
Pulse Diode Forward Current	I _{SM}		-	-	-15	
Body Diode Voltage	V_{SD}	I _S = -3.9 A, V _{GS} = 0 V	-	-0.9	-1.2	V
Body Diode Reverse Recovery Time t _{rr}			-	13	25	ns
Body Diode Reverse Recovery Charge	Q _{rr}	1 20 A dl/dt 100 A/: T 05 00	-	5.5	12	nC
Reverse Recovery Fall Time	ta	$I_F = -3.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$	-	7.5	-	ns
Reverse Recovery Rise Time	t _b		-	5.5	_	

Notes

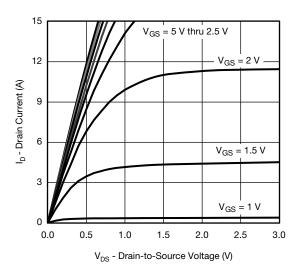
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

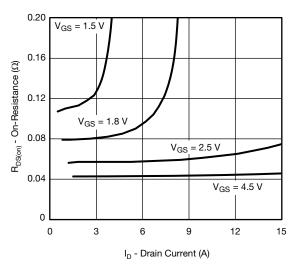




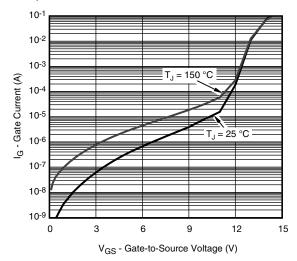
Gate Current vs. Gate-to-Source Voltage



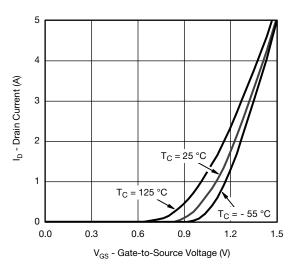
Output Characteristics



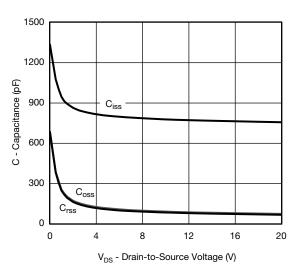
On-Resistance vs. Drain Current and Gate Voltage



Gate Current vs. Gate-to-Source Voltage

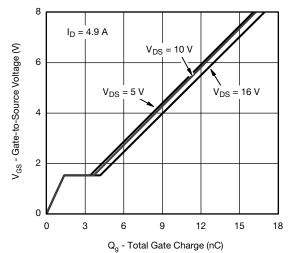


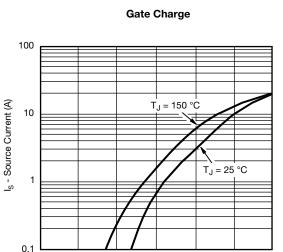
Transfer Characteristics



Capacitance







V_{SD} - Source-to-Drain Voltage (V) **Source-Drain Diode Forward Voltage**

0.6

0.8

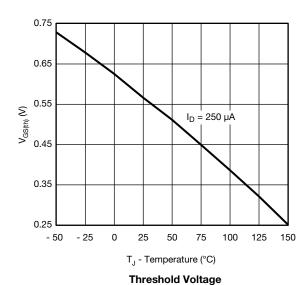
1.0

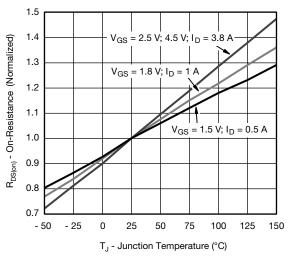
1.2

0.2

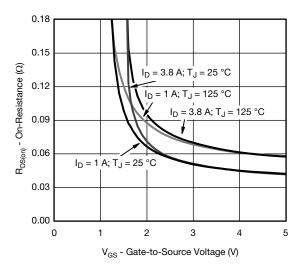
S13-2636-Rev. A, 30-Dec-13

0

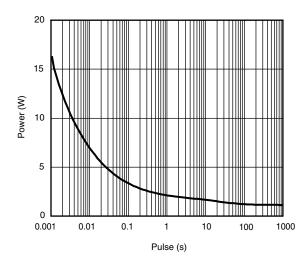




On-Resistance vs. Junction Temperature

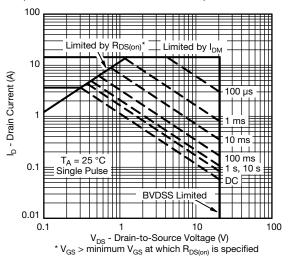


On-Resistance vs. Gate-to-Source Voltage

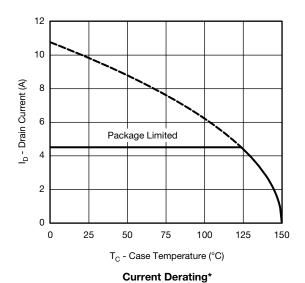


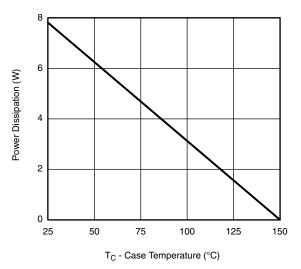
Single Pulse Power, Junction-to-Ambient





Safe Operating Area, Junction-to-Ambient



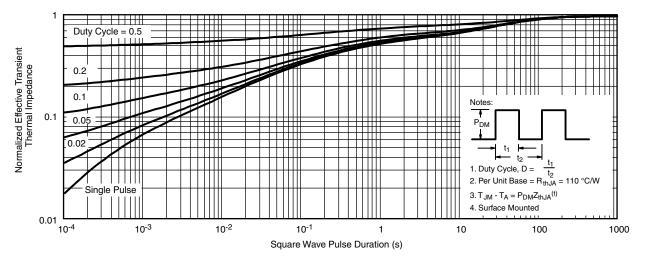


Power Derating

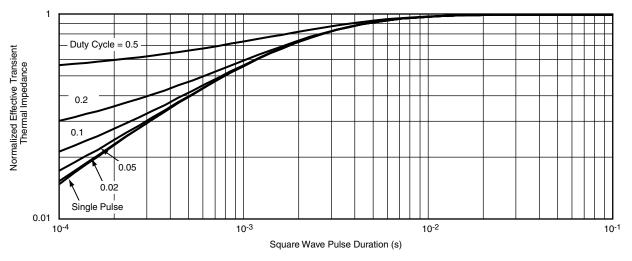
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^{*} The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

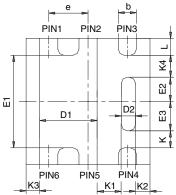
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262936.

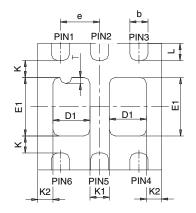




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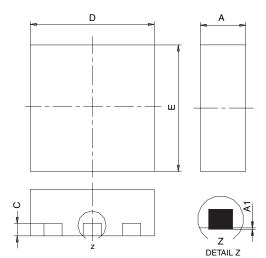
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

		SINGLE PAD					DUAL PAD					
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	,	0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP		
K1	0.400 TYP				0.016 TYP	YP 0.320 TYP			0.013 TYP			
K2	0.240 TYP 0.009			0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP	1	0.009 TYP								
K4	0.355 TYP 0.014 TYP											
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
ECNI- C C	7404 D	. 0 00 1	. 07									

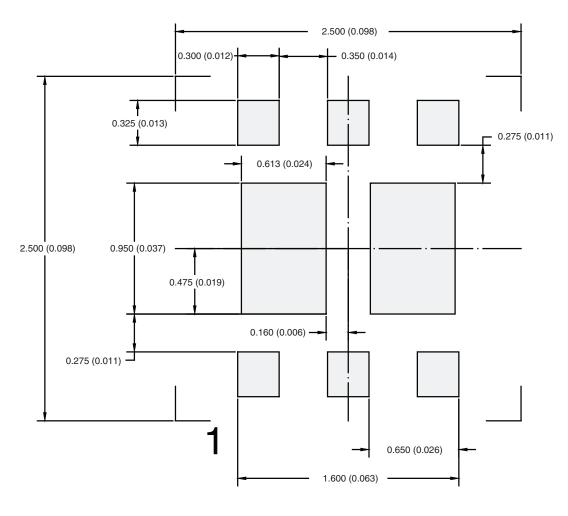
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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Vishay

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Revision: 02-Oct-12 Document Number: 91000